

NSBC115TPDP6T5G

NSBC115TPDP6T5G Information

unvie televener.com	 NSBC115TPDP6T5G ON Semiconductor Discrete Semiconductor Products Transistors - Bipolar (BJT) - Arrays, Pre-Biased TRANS NPN/PNP PREBIAS SOT963 SOT-963 For the pricing/inventory/lead time, please contact	
For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

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NSBC115TPDP6T5G Specifications

Manufacturer Part NumberNSBC115TPDP6T5GManufacturerON SemiconductorCategoryDiscrete Semiconductor ProductsTransitors - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Base (R2) (Ohms)-Vc Saturation (Max) @ Ib, Ic250mV@ 1mA, 10mAVce Saturation (Max) @ Ib, Ic500nACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mW			
CategoryDiscrete Semiconductor ProductsCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lo (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Lc, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nA	Manufacturer Part Number	NSBC115TPDP6T5G	
InterferenceTransistor - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lc) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Lc, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nA	Manufacturer	ON Semiconductor	
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Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min @ Ic, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Package	SOT-963	
Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Series	-	
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Resistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Current - Collector (Ic) (Max)	100mA	
Resistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Voltage - Collector Emitter Breakdown (Max)	50V	
DC Current Gain (hFE) (Min) @ Ic, Vce 160 @ 5mA, 10V Vce Saturation (Max) @ Ib, Ic 250mV @ 1mA, 10mA Current - Collector Cutoff (Max) 500nA Frequency - Transition -	Resistor - Base (R1) (Ohms)	100k	
Vce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Resistor - Emitter Base (R2) (Ohms)	-	
Current - Collector Cutoff (Max)500nAFrequency - Transition-	DC Current Gain (hFE) (Min) @ Ic, Vce	160 @ 5mA, 10V	
Frequency - Transition -	Vce Saturation (Max) @ Ib, Ic	250mV @ 1mA, 10mA	
	Current - Collector Cutoff (Max)	500nA	
Power - Max 339mW	Frequency - Transition	-	
	Power - Max	339mW	
Mounting Type Surface Mount	Mounting Type	Surface Mount	
Package / Case SOT-963	Package / Case	SOT-963	
Supplier Device Package SOT-963	Supplier Device Package	SOT-963	
Report errors?		Report errors?	

NSBC115TPDP6T5G Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

NSBC115TPDP6T5G Payment Methods





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